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(71)Applicant: NIPPON TELEGR & TELEPH CORP

<NTT>

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(72)Inventor: KIMURA TAKAO

ONOSE KATSUHIDE TANAKA HARUYORI

(54) RESIST MATERIAL AND PHOTOSENSITIVE RESIN COMPOSITION

(57) Abstract:

PURPOSE: To obtain the resist material of an alkaline development type having a high glass transition temp. and excellent O2 RIE resistance by incorporating an oxysilane ring into a part or the whole of a multifunctional alkoxysilane.

CONSTITUTION: The oxysilane ring is incorporated into a part or the whole of the multifunctional alkoxysilane. Namely, the siloxane bond is first made into skeleton structure in order to solve the problem that the resist does not contain a silicon component and is, therefore, poor in the O2 RIE resistance, by which the Q2 RIE resistance is enhanced. The glass transition temp. is in creased by adopting the chemical structure of a ladder type by the use of the multifunctional alkoxysilane as a raw material. The oxysilane ring is introduced and the alkaline solubility is enhanced by the hydroxyl group subjected to the ring opening thereof. The multifunctional alloxysilane having the oxysilane ring to be used is exemplified by 3-glycidoxy propyl methoxysilane, etc. The non-swelling negative type resist which has high oxygen plasma resistance and allows alkaline development is obtd. in this way.

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